

In the Claims

The following is a complete listing of the claims and replace all prior claims in the application:

- 1 1. (Withdrawn) A method for forming self-pinned abutted junction heads,
2 comprising:
3 forming a first self-pinned layer having a first magnetic orientation, the first layer
4 having a first end, a second end and central portion;
5 forming a second self-pinned layer over only the central portion of the first self-
6 pinned layer, an interlayer being disposed between the first and second self-pinned
7 layers;
8 forming a free layer in a central region over the second self-pinned layer; and
9 forming a first and second hard bias layers over the first and second ends of the
10 first self-pinned layer respectively, the first and second hard bias layer abutting the free
11 layer, the first and second end of the first self-pinned layer extending under the hard bias
12 layers at the first and second ends.
- 1 2. (Withdrawn) The method of claim 1 further comprising forming a spacer
2 layer over the first self-pinned layer and forming a first and second seed layer between
3 the first and second hard bias layer and the spacer layer.

1 3. (Withdrawn) The method of claim 2 further comprising forming
2 amorphous layers between the spacer and the first and second seed layers, the amorphous
3 layer stopping epitaxial growth between the first self-pinned layer and the first and
4 second hard bias layers.

1 4. (Withdrawn) The method of claim 1 further comprising forming
2 amorphous layers between the first self-pinned layer and the first and second hard bias
3 layers for stopping epitaxial growth between the first self-pinned layer and the first and
4 second hard bias layers.

1 5. (Withdrawn) The method of claim 1 further comprising forming first and
2 second leads over the first and second hard bias layers.

1 6. (Withdrawn) The method of claim 1, wherein the forming the first and
2 second hard bias layers further comprises electrically coupling the first and second hard
3 bias layers to the free layer to allow sense current to pass through the free layer.

1 7. (Withdrawn) The method of claim 1, wherein forming the first and
2 second hard bias layers over the first self-pinned layer further comprises providing a
3 coupling of the self-pinned layers and the free layer to the first and second hard bias
4 layers, the first and second hard bias layers being cooler than the central region to
5 maintain pinning of the first and second hard bias layers, the maintenance of the pinning
6 of the first and second hard bias layers maintaining the pinning of the free layer.

1 8. (Withdrawn) The method of claim 1, wherein the forming the free layer
2 further comprises forming the free layer with a length selected for a desired track width.

1 9. (Currently Amended) A self-pinned abutted junction magnetic read
2 sensor, comprising:

3 a first self-pinned layer having a first magnetic orientation, the first self-pinned
4 layer having a first end, a second end and central portion, the first and second end of the
5 first self-pinned layer having a side surface, top surface and bottom surface;

6 a second self-pinned layer formed over only the central portion of the first self-
7 pinned layer, an interlayer being disposed between the first and second self-pinned
8 layers;

9 a free layer formed in a central region over the second self-pinned layer; and

10 a first and second hard bias layers formed over the top surface of the first and
11 second ends of the first self-pinned layer respectively, the first and second hard bias layer
12 abutting the free layer, the top surface of the first and second end of the first self-pinned
13 layer extending under the hard bias layers at the first and second ends and contacting the
14 hard bias layer along the top surface of the first and second ends of the first self-pinned
15 layer.

1 10. (Previously Presented) The sensor of claim 9 further comprising a
2 spacer layer formed over the first self-pinned layer and a first and second seed layer
3 disposed between the first and second hard bias layer and the spacer layer.

1 11. (Previously Presented) The sensor of claim 10 further comprising
2 amorphous layers formed between the spacer and the first and second seed layers, the
3 amorphous layer stopping epitaxial growth between the first self-pinned layer and the
4 first and second hard bias layers.

1 12. (Previously Presented) The sensor of claim 9 further comprising
2 amorphous layers formed between the first self-pinned layer and the first and second hard
3 bias layers for stopping epitaxial growth between the first self-pinned layer and the first
4 and second hard bias layers.

1 13. (Previously Presented) The sensor of claim 9 further comprising
2 first and second leads formed over the first and second hard bias layers.

1 14. (Previously Presented) The sensor of claim 9, wherein the first and
2 second hard bias layers are electrically coupled to the free layer to allow sense current to
3 pass through the free layer.

1 15. (Previously Presented) The sensor of claim 9, wherein the first and
2 second hard bias layers are cooler than the central region to providing stable pinning of
3 the free layer.

1 16. (Previously Presented) The sensor of claim 9, wherein the free layer
2 includes a length selected for a desired track width.

1 17. (Currently Amended) A magnetic storage system, comprising:
2 a moveable magnetic storage medium for storing data thereon;
3 an actuator positionable relative to the moveable magnetic storage medium; and
4 a magnetoresistive sensor, coupled to the actuator, for reading data from the
5 magnetic recording medium when position to a desired location by the actuator, wherein
6 the magnetoresistive sensor further comprises:
7 a first self-pinned layer having a first magnetic orientation, the first self-
8 pinned layer having a first end, a second end and central portion, the first and second end
9 of the first self-pinned layer having a side surface, top surface and bottom surface;
10 a second self-pinned layer formed over only the central portion of the first
11 self-pinned layer, an interlayer being disposed between the first and second self-pinned
12 layers;
13 a free layer formed in a central region over the second self-pinned layer;
14 and
15 a first and second hard bias layers formed over the top surface of the first
16 and second ends of the first self-pinned layer respectively, the first and second hard bias
17 layer abutting the free layer, the top surface of the first and second end of the first self-
18 pinned layer extending under the hard bias layers at the first and second ends and
19 contacting the hard bias layer along the top surface of the first and second ends of the
20 first self-pinned layer.

1 18. (Previously Presented) The magnetic storage system of claim 17
2 further comprising a spacer layer formed over the first self-pinned layer and a first and
3 second seed layer disposed between the first and second hard bias layer and the spacer
4 layer.

1 19. (Previously Presented) The magnetic storage system of claim 18
2 further comprising amorphous layers formed between the spacer and the first and second
3 seed layers, the amorphous layer stopping epitaxial growth between the first self-pinned
4 layer and the first and second hard bias layers.

1 20. (Previously Presented) The magnetic storage system of claim 17
2 further comprising amorphous layers formed between the first self-pinned layer and the
3 first and second hard bias layers for stopping epitaxial growth between the first self-
4 pinned layer and the first and second hard bias layers.

1 21. (Previously Presented) The magnetic storage system of claim 17
2 further comprising first and second leads formed over the first and second hard bias
3 layers.

1 22. (Previously Presented) The magnetic storage system of claim 17,
2 wherein the first and second hard bias layers are electrically coupled to the free layer to
3 allow sense current to pass through the free layer.

1 23. (Previously Presented) The magnetic storage system of claim 17,
2 wherein the first and second hard bias layers are cooler than the central region to
3 providing stable pinning of the free layer.

1 24. (Previously Presented) The magnetic storage system of claim 17,
2 wherein the free layer includes a length selected for a desired track width.

1 25. (Currently Amended) A self-pinned abutted junction magnetic read
2 sensor, comprising:
3 a first means for providing a first self-pinned layer having a first magnetic
4 orientation, the first means having a first end, a second end and central portion, the first
5 and second end of the first self-pinned layer having a side surface, top surface and bottom
6 surface;
7 second means for providing a second self-pinned layer formed over only the
8 central portion of the first means, an interlayer being disposed between the first and
9 second means;
10 a third means for providing a free layer formed in a central region over the second
11 means; and
12 a fourth and fifth means for providing first and second hard bias layers, the fourth
13 and fifth means being formed over the top surface of the first and second ends of the first
14 means respectively, the first and second means abutting the third means, the top surface
15 of the first and second end of the first means extending under the fourth and fifth means
16 at the first and second ends and contacting the fourth and fifth means along the top
17 surface of the first and second ends of the first means.

1 26. (Currently Amended) A magnetic storage system, comprising:
2 a moveable magnetic storage means for storing data thereon;
3 an actuator positionable relative to the moveable magnetic storage medium; and
4 a magnetoresistive sensor, coupled to the actuator, for reading data from the
5 magnetic recording medium when position to a desired location by the actuator, wherein
6 the magnetoresistive sensor further comprises:
7 a first means for providing a first self-pinned layer having a first magnetic
8 orientation, the first means having a first end, a second end and central portion, the first
9 and second end of the first self-pinned layer having a side surface, top surface and bottom
10 surface;
11 second means for providing a second self-pinned layer formed over only
12 the central portion of the first means, an interlayer being disposed between the first and
13 second means;
14 a third means for providing a free layer formed in a central region over the
15 second means; and
16 a fourth and fifth means for providing first and second hard bias layers, the
17 fourth and fifth means being formed over the top surface of the first and second ends of
18 the first means respectively, the first and second means abutting the third means, the top
19 surface of the first and second end of the first means extending under the fourth and fifth
20 means at the first and second ends and contacting the fourth and fifth means along the top
21 surface of the first and second ends of the first means.